Valley-reversible Berry phase effects in 2D valley-half-semiconductors

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(Dated: June 17, 2021)

Manipulating valley-dependent Berry phase effects provides remarkable opportunities for both fundamental research and practical applications. Here, by referring to effective model analysis, we propose a general scheme for realizing topological magneto-valley phase transitions. More importantly, by using valley-half-semiconducting VSi$_2$N$_4$ as an outstanding example, we investigate valley-reversible Berry phase effects which drive the change-in-sign valley anomalous transport characteristics via external means such as biaxial strain, electric field, and correlation effects. As a result, this gives rise to quantized versions of valley anomalous transport phenomena. Our findings not only uncover a general framework to control valley degree of freedom, but also motivate further research in the direction of multifunctional quantum devices in valleytronics and spintronics.

Introduction.— Recent advances in valleytronics are mainly based on the paradigm of time-reversal-connected valleys, which generates valley polarization by an external field, dynamically or statically [1, 2]. However, for achieving widespread applications of valleytronics, intrinsic properties are to be prioritized higher than external tunability. More importantly, intrinsic valleytronics materials hosting spontaneous valley polarization are most desirable, owing to their advantages of robustness, power efficiency, and simplicity in operation. In this regard, alternatives to the existing paradigms are intensively sought after. Recently, the proposal of two-dimensional (2D) ferrovalley materials has laid out a new magneto-valleytronics composite paradigm based on spontaneous valley polarization induced by the integrated effects of magnetic order and spin-orbit coupling (SOC), which can radically reduce additional costs of the applied external fields [3]. Specifically, when valley couples with intrinsic ferromagnetic (FM) order, the valley-dependent Berry phase effects can generate emergent valley anomalous transport phenomena — e.g., valley Hall effect [4–7] and valley Nernst effect [8, 9]) — making it possible to realize high-performance quantum devices thus raising an intensive interest in materials systems which host magneto-valley traits.

From the perspective of potential applications in valleytronics, exploring various phase transitions in 2D magneto-valley materials has played a vital role in promoting our understanding, discovery and characterization of new quantum states of matter. A general law of phase transitions is that they can drive not only novel quantum states but also intriguing physical properties. However, possibly due to the fewer number of 2D ferrovalley materials [3, 10–14] and the difficulty in characterizing the magnetic ordering and topological phase transitions, high-quality magneto-valley material candidates with a wide range of phase transitions have been scarcely discussed. On the other hand, an interplay between different phase transitions accompanied by distinct valley anomalous transport manifestations in such materials has not been seriously considered yet, which poses a great challenge for the research on potential high-performance valleytronics devices.

A crucial but thought-provoking issue for magneto-valley coupling (MVC) is finding a way to effectively generate spontaneous valley polarization utilizing the spin degree of freedom, and thereby lead to a revolution in magneto-valley-based information storage and operation principles. To tackle current challenges of valleytronics, we break out present ferrovalley paradigm to provide a general classification of MVC states through an effective model analysis, where the low energy electronic inter-valley nature enjoys a giant valley splitting with fully spin-polarized fermions. Consistent with the model, as a concrete example, VSi$_2$N$_4$ showcases emerging MVC phases — including valley-half-semiconductor (VHSC), valley-half-semimetal (VHSM) as well as valley quantum anomalous Hall (VQAH) states — transitions between which can be controlled by using external stimuli such as biaxial strain, electric field and correlation effects. Remarkably, we find that topological phase transitions with MVC can exhibit valley-dependent Berry phase effects which manifest in prominent valley-reversible anomalous transport fingerprints.

Valley-half-semiconductors and their topological phase transitions.— According to the relationship between the
valence band maximum (VBM) and conduction band minimum (CBM) of the same spin channel at the Fermi level, MVC gives rise to a wide spectrum of quantum phase transitions ranging from gapped to gapless ones. To better capture the key physics underlying topological phase transitions, we construct a simple tight-binding (TB) model for describing the topological phase transitions starting from the VHSC state, is inevitably encountered [Fig. 1(b)]: it is gapless at K’ valley but it is gapped at K valley. The gapless crossing point is two-fold degenerate with a linear dispersion, similar to that of Weyl semimetals. In Fig. 1(c), the gap reopening at K’ valley indicates a topological phase transition, and the VQAH state is confirmed by a nonzero Chern number (C = 1). Further increasing the parameter e_1 will force K valley to first close the gap and then reopen it again, as shown in Figs. 1(d) and 1(e). The summary of topological phase transitions is shown in Fig. 1(f). Note that the SOC has been taken into account in our model [16], and therefore the emergence of MVC states having 100% spin polarization is remarkable and promising for spin-valleytronics [17–20].

A unique interplay between valley degree of freedom, magnetism, and topology provides an excellent platform for researching valley-related anomalous transport properties of MVC states, realizing a rich set of exotic quantum phenomena, such as valley anomalous Hall effect (VAHE), valley anomalous Nernst effect (VANE), as well as valley magneto-optical Kerr effect (VMOKE) and valley magneto-optical Faraday effect (VMOFE). Specifically, pursuing a single material that simultaneously exhibits topological phase transitions and valley-reversible Berry phase effects has been rarely done to date, although such a material would be highly valuable for the multifunctional miniaturized devices. In addition to considering artificially constructed MVC heterostructures, an alternative is to seek intrinsic MVC materials that can harbor topological phase transitions driven by external means, such as biaxial strain, electric field, and correlation effects.

High-quality candidate materials.— In this work not only do we provide a classification of MVC states, but also propose a series of MVC materials [Figs. 2(a) and 2(b)], including 2D ferromagnetic VSi_2N_4 as well as other eleven M_A2Z_4 (M = V, Nb; A = Si, Ge; Z = N, P, As) candidates [21, 22]. All these candidate materials form on a hexagonal lattice with the same magnetic space group that has been employed above. While aforementioned MVC states and their topological phase transitions exist in all materials, below we focus on one representative —
FIG. 2. (a-b) The top and side views of $MA_2Z_4$ materials family. The dashed lines in (a) indicate the 2D primitive cell. (c) The Brillouin zone of $MA_2Z_4$. (d) The band structures of VSi$_2$N$_4$ calculated by the hybrid functional without SOC (left panel) and with SOC (right panel). (e) The stress-strain curve of VSi$_2$N$_4$. Top $x$-axis plots the whole strain range of $0\% \sim 30\%$, while bottom $x$-axis plots the small strain range of $0\% \sim 3\%$. The colors indicate the magnitudes of the band gap, and the corresponding Chern number ($C$) is marked. The evolution of band structure (f) and orbital compositions at band edge (g) under the strain of $0\% \sim 2\%$. Various fully spin-polarized valley topological states emerges, including VHSC (0%), VHSM (1.4%), VQAH (1.6%), VHSM (1.75%), and VHSC (2%).

VSi$_2$N$_4$ – and discuss the rest of materials in the Supplemental Material (see Figs. S1 and S2) [16].

The electronic band structure of VSi$_2$N$_4$, which is a fully spin-polarized semiconductor with a small direct band gap (0.24 eV) at K/K’ valley in spin up channel and with a large indirect band gap (3.19 eV) in spin down channel, is shown in Fig. 2(d). When SOC is taken into account, VSi$_2$N$_4$ evolves into a novel VHSC state with a giant valley splitting of 102.3 (27.3) meV at the valence (conduction) band edge. More importantly, VSi$_2$N$_4$ possesses an “ultra-clean” linear band dispersion around K and K’ valleys in the energy range of $[-0.7, +1.2]$ eV, which suppresses the influence of irrelevant trivial bands for valley performance. The linear band dispersion ensures high Fermi velocity of about $0.4 - 0.5 \times 10^6$ m/s along different momentum directions, which is of the same order as that of graphene [23]. This promotes VSi$_2$N$_4$ into one of the most appealing candidates when comparing it with currently considered ferrovalley materials.

While VSi$_2$N$_4$ is a unique long-sought VHSC material, it can also host various fully spin-polarized MVC topological states under external means such as biaxial strain, electric field, and correlation effects. Taking biaxial strain as an example (the cases of electric field and correlation effects are shown in Figs. S5 and S6 [16]), we predict strained VSi$_2$N$_4$ to exhibit various MVC states, covering VHSC, VHSM, and VQAH states. As shown in Fig. 2(f), by increasing strain within a reasonable range ($0\% \sim 2\%$), the VHSC state (0%) undergoes topological phase transitions that can be identified by the closing and reopening of band gaps at K’ and K valleys, resulting in the VHSM (1.4%), VQAH (1.6%), VHSM (1.75%), and VHSC (2%) states. The gap evolution together with corresponding Chern numbers is summarized in Fig. 2(e). Furthermore, the orbital-projected band structures of MVC states [Fig. 2(g)] are another indicator for topological phase transitions. In the balanced state of VSi$_2$N$_4$, the VBM is dominated by the $d_{xy}$ and $d_{x^2-y^2}$ orbitals of V atoms, and the CBM mainly comes from the $d_{z^2}$ orbital. At the strain of 1.4%, the orbital compositions reverse at K’ valley, driving the system into the VQAH state; further increasing strain to 1.75%, the orbital inversion occurs also at K valley, restoring the system to the VHSC state.

Valley-reversible Berry phase effects.— An in-depth investigation of MVC topological phase transitions provides a platform for exploring valley-related anomalous transport phenomena. In this context, it is remarkable that VSi$_2$N$_4$, while hosting topological phase transitions,
to be \( \frac{\alpha}{e} \) rather similar to that of VMOKE. The unit of VANE is set respectively. The results of VMOFE (not shown here) are disregarding the VHSC state (0%), for which the calculated exhibits also valley-reversible Berry phase effects. Regarding the VHSC state (0%), for which the calculated \( k \)-resolved Berry curvature \( \Omega(k) \) is shown in Fig. 3(a), one can clearly identify the hot spots in the Berry curvature around two valleys with opposite signs and different magnitudes. By introducing a tiny biaxial strain, the VHSC state experiences a topological phase transition into the VQAH state, bridged by the VHSM state. Within the strain of 1.4% ~ 1.6%, the sign of \( \Omega(k) \) at \( K' \) valley flips [Fig. 3(b)]. Further increasing strain from 1.6% to 2%, \( K \) valley also experiences a topological phase transition, akin to the case of \( K' \) valley, resulting in the sign change of \( \Omega(k) \) at \( K \) valley [Fig. 3(c)]. Such dynamics of \( \Omega(k) \) is bound to influence the valley-related anomalous transport phenomena such as VAHE, VANE, VMOKE, and VMOFE.

Our predictions concerning the valley-related anomalous transport phenomena are presented in Fig. 3. Since VAHE is calculated by the integration of \( \Omega(k) \) in a small region centered at each valley, the sign changes of VAHE are in full accordance with \( \Omega(k) \) during the topological phase transitions. This is also the case for VANE as well as VMOKE and VMOFE. The former is calculated by integrating the Berry curvature together with a weighting factor around each valley (see Eq. S2 of Supplemental Material). The latter phenomenon can be actually regarded as the \( ac \) counterpart of VAHE. Physically, these anomalous transport phenomena are intimately related to each other. Therefore, the change in their signs strongly depends on the nature of topological phase transitions, exhibiting exotic valley-reversible Berry phase effects.

Interestingly, due to the different magnitudes of \( \Omega(k) \) at two valleys, a net fully spin-polarized valley current is produced by the anomalous Hall, anomalous Nernst, and magneto-optical effects. Notably, the VQAH phase emerges during the phase transition, accompanied by a quantized anomalous Hall conductivity \( \sigma_{xy} = e^2/h \) [second row of Fig. 3(b)]. Besides, one can utilize the non-contact magneto-optical technique [24–26] to detect this topological phase [27–30]. For a VQAH state, the central physical idea is that the Maxwell’s equations have to be modified by adding an axion term \((\Theta \alpha/4\pi^2)E \cdot B \) (here \( \Theta \) is magnetoelectric polarizability and \( \alpha = e^2/hc \) is fine structure constant) into the usual Lagrangian [31]. In this way, the magneto-optical Kerr (\( \theta_K \)) and Faraday (\( \theta_F \)) rotation angles turn out to be quantized in the low-frequency limit, that is, \( \theta_K \simeq -\pi/2 \) and \( \theta_F \simeq C\alpha \) (\( C \) is the Chern number) [32, 33]. In the bottom of Fig. 3(b), one can clearly observe the quantization behavior of \( \theta_K \) and \( \theta_F \) in the low-frequency limit.

Generally, the tunable sign of \( \Omega(k) \) has been witnessed by reversing the magnetization [3] and ferroelectric polarization [34]. However, these two means seem to be suboptimal and often suffer from various drawbacks, making it difficult to utilize this effect. As an alternative avenue, the manipulation by a small biaxial strain is more suitable for practical purposes. It is worth noting that topological phase transitions through biaxial strain may not only change the sign of anomalous transport characteristics but also modify their magnitude, and more importantly, the mediated quantization of transport characteristics is indispensable for experimental observation.

**Conclusion.**—In this Letter, we introduce a general framework to realize topological magneto-valley phase transitions in 2D VHSC, and we propose a series of feasible candidate materials harboring novel valley-reversible Berry phase effects, which are triggered by external means such as biaxial strain, electric field, and correlation effects. Taking VSi\(_2\)N\(_4\) as a representative, we demonstrate that such intrinsic VHSC states display unique fully spin-polarized valley index. The proposal of valley-reversible Berry phase effects and high-quality materials realization greatly expand the ferrovalley family and
provide an exciting playground for spintronics and valleytronics applications.

This work is supported by the National Key R&D Program of China (Grant No. 2020YFA0308800), the National Natural Science Foundation of China (Grant Nos. 11734003, 11874085, 12047512, and 12004028), and the Project Funded by China Postdoctoral Science Foundation (Grant Nos. 2020M680011 and 2021T140057). Y.M. acknowledges the Deutsche Forschungsgemeinschaft (DFG, German Research Foundation) – TRR 288 – 422213477 (project B06). Y.M., W.F., and Y.Y. acknowledge the funding under the Joint Sino-German Research Projects (Chinese Grant No. 12061131002 & German Grant No. 1731/10-1) and the Sino-German Mobility Programme (Grant No. M-0142).

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